TOSHIBA PHOTOCOUPLER

TLP762J(D4), TLP762JF(D4), TLP763J(D4), TLP763JF(D4)

ATTACHMENT: SPECIFICATIONS FOR VDE0884 OPTION: (D4)

Types: TLP762J, TLP762JF, TLP763J, TLP763JF

Type designations for 'Option: (D4)', which are tested under VDE0884 requirements.

: TLP762J (D4-LF1) **D4** : VDE0884 option

> LF1 : lead bend

Note: Use Toshiba standard type number for safety standard application.

Ex. TLP762J (D4-LF1) \rightarrow TLP762J

VDE0884 ISOLATION CHARACTERISTICS

DESCRIPTION	SYMBOL	RATING	UNIT
Application Classification (DIN VDE0110 Teil 2/01.89, Table 1)			
for rated mains voltage ≤ 300 V _{RMS}		I-IV	_
for rated mains voltage \leq 600 V _{RMS}		I - Ⅲ	
Climatic Classification		40/100/21	
(DIN IEC68 Teil 1/09.80)		40/100/21	
Pollution Degree (DIN VDE0110 Teil 2/01.89)		2	_
Maximum Operating Insulation Voltage	V _{IORM}	1130	Vpk
Input to output Test Voltage, Method A			
Vpr=1.5×V _{IORM} Type and Sample Test	Vpr	1695	Vpk
t _p =60s, Partial Discharge<5pC			
Input to output Test Voltage, Method B			
$Vpr = 1.875 \times V_{IORM}$, 100% Production Test	Vpr	2120	Vpk
t _p =1s, Partial Discharge<5pC			
Highest Permissible Overvoltage	Vmp	6000	Vpk
(Transient Overvoltage, t _{pr} =10s)	$v_{ m TR}$	0000	V PK
Safety Limiting Values (Max. permissible ratings in case of			
fault, also refer to thermal derating curve)			
Current (Input current I _F , Psi=0)	Isi	400	mA
Power (Output or Total Power Dissipation)	Psi	700	mW
Temperature	Tsi	150	°C
Insulation Resistance, V _{IO} =500V, Ta=25°C	Rsi	\geqq 10^{12}	Ω
$V_{IO} = 500 V$, $Ta = Tsi$	1601	\geq 10^{9}	42

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ΙΝSΗΙ ΔΤΙΩΝ	RFI ATFD	SPECIFICATIONS
IIIJOLATION		

INSULATION RELATED SPECIFICATIONS						
		7.62mm pitch	10.16mm pitch			
		TLPxxx type	TLPxxxF type			
Minimum Creepage Distance (*)	Cr	7.0mm	8.0mm			
Minimum Clearance (*)	Cl	7.0mm	8.0mm			
Minimum Insulation Thickness	ti	0.5mm				
Comperative Tracking Index	CTI	175				
(DIN IEC112/VDE0303, Part 1)		(VDE0110 Teil 2/	(01.89 Group II a)			

- (*) in accordance with DIN VDE0110 Teil 2/01.89, Table 2, & 4
- 1. If a printed circuit is incorporated, the creepage distance and clearance may be reduced below this value (e. g. at a standard distance between soldering eye centres of 7.5mm). If this is not permissible, the user shall take suitable measures.
- 2. This photocoupler is suitable for 'safe electrical isolation' only within the safety limit data. Maintenance of the safety data shall be ensured by means of protective circuits.







